



DATA SHEET

SEMICONDUCTOR

W005M THRU W10M

SINGLE-PHASE SILICON BRIDGE

Reverse Voltage - 50 to 1000 Volts
Forward Current - 1.5 Amperes



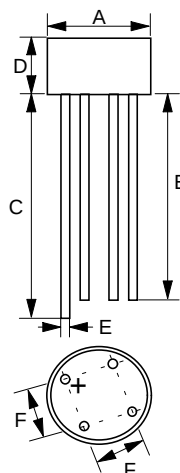
WOM

FEATURES

- Rating to 1000V PRV
- Ideal for printed circuit board
- Low forward voltage drop, high current capability.
- Reliable low cost construction utilizing molded epoxy technique results in inexpensive product
- The plastic material has UL flammability classification 94V-0

MECHANICAL DATA

- Case : Molded plastic
- Polarity: As marked on Body
- Weight : 0.05 ounces, 1.42grams
- Mounting position : Any



WOG		
DIM.	MIN.	MAX.
A	8.90	9.30
B	25.4	-
C	27.9	-
D	5.10	5.60
E	0.70	0.80
F	4.60	5.60
All Dimensions in millimeter		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	W005M	W01M	W02M	W04M	W06M	W08M	W10M	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @TA=25 °C	I _(AV)	1.5							A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I _{FSM}	50							A
Maximum forward Voltage at 1.0A DC	V _F	1.0							V
Maximum DC Reverse Current @T _J =25 °C at Rated DC Blocking Voltage @T _J =125 °C	I _R	5.0 500							uA
I ² t Rating for fusing (t < 8.3ms)	I ² t	10.4							A ² S
Typical Junction Capacitance per element (Note 1)	C _J	20							pF
Typical Thermal Resistance (Note 2)	R _{θJA}	36							°C/W
Operating Temperature Range	T _J	-55 to +150							°C
Storage Temperature Range	T _{STG}	-55 to +150							°C

NOTES : 1.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2.Thermal Resistance Junction to Ambient

DEVICE CHARACTERISTICS

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